

Substitute for form 1449A/B/PTO  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (Use as many sheets as necessary)				<b>Complete if Known</b>	
Application Number		NEW- 101736617			
Filing Date		December 12, 2003			
First Named Inventor		Kristy A. Campbell			
Art Unit		N/A 2829B			
Examiner Name		Not Yet Assigned V. Yevsikov			
Attorney Docket Number		M4065.0698/P698-A			
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U.S. PATENT DOCUMENTS							
Examiner Initials*	Cite No. <sup>1</sup>	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	
		Number-Kind Code <sup>2</sup> (if known)					
✓	AA	6,473,332		10/2002	Ignatiev et al.	/	
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Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>4</sup>
		Country Code <sup>3</sup>	Number <sup>4</sup> -Kind Code <sup>5</sup> (if known)				
✓	BA	WO	97/48032	12/18/1997	Kozicki et al.		
✓	BB	WO	99/28914	06/10/1999	Kozicki et al.		

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. <sup>1</sup> Applicant's unique citation designation number (optional). <sup>2</sup> See Kinds Codes of USPTO Patent Documents at [www.uspto.gov](http://www.uspto.gov) or MPEP 901.04. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup> For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup> Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. <sup>6</sup> Applicant is to place a check mark here if English language Translation is attached.

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
✓	CA	Abdel-All, A.; Elshafie, A.; Elhawary, M.M., DC electric-field effect in bulk and thin-film Ge <sub>5</sub> As <sub>38</sub> Te <sub>57</sub> chalcogenide glass, Vacuum 59 (2000) 845-853.	
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				First Named Inventor	Kristy A. Campbell
				Art Unit	2529
				Examiner Name	Not Yet Assigned - Yevsi Kov
Sheet	3	of	8	Attorney Docket Number	M4065.0698/P698-A

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Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

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Sheet	4	of	8	Attorney Docket Number	M4065.0698/P698-A

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			Filing Date	December 12, 2003	
			First Named Inventor	Kristy A. Campbell	
			Art Unit	2829	
			Examiner Name	Not Yet Assigned - Yelviskov	
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				First Named Inventor	Kristy A. Campbell
				Art Unit	N/A-2829
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		First Named Inventor	Kristy A. Campbell		
		Art Unit	2825 2829 B		
		Examiner Name	R. Rocchegiani VYEVSIKA		
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		Examiner Name	R. Reochegiani Yersikov		
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↑	**AV1	4,177,474	12/1979	Ovshinsky	
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V	**AR3	5,512,328	4/1996	Yoshimura et al.	
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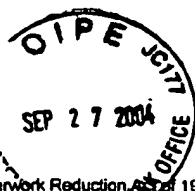
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				Art Unit	2829
				Examiner Name	R. Rocchegiani Yevsi Kov
Sheet	4	of	5	Attorney Docket Number	M4065.0698/P698-A

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		Application Number	10/736,617		
		Filing Date	December 17, 2003		
		First Named Inventor	Kristy A. Campbell		
		Art Unit	2828 9		
		Examiner Name	<del>R. Rocchegiani</del> Yeusikov		
Sheet	5	of	5	Attorney Docket Number	M4065.0698/P698-A

FOREIGN PATENT DOCUMENTS							
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>2</sup>
		Country Code <sup>3</sup>	Number <sup>4</sup> -Kind Code <sup>5</sup> (if known)				
VY	**BA	JP	5-6126916	10/19981	Akira et al.		
VY	**BB	WO	00/48196	08/17/2000	Kozicki et al.		
VY	**BC	WO	02/21542	03/14/2002	Kozicki et al.		

Examiner Signature	V. Yeusikov	Date Considered	03/01/05
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